

SavantIC Semiconductor

Product Specification

Silicon PNP Power Transistors 2N5605 2N5607 2N5609 2N5611

DESCRIPTION

- With TO-66 package
- Excellent safe operating area
- Low collector saturation voltage

APPLICATIONS

- For general-purpose amplifier ;
and switching applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

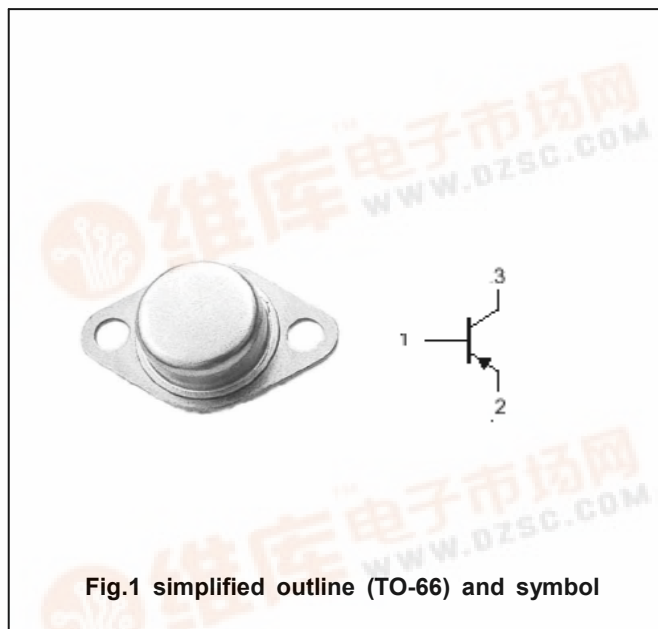


Fig.1 simplified outline (TO-66) and symbol

Absolute maximum ratings($T_a = \square$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	2N5605	-80	V
		2N5607/5609	-100	
		2N5611	-120	
V_{CEO}	Collector-emitter voltage	2N5605	-60	V
		2N5607/5609	-80	
		2N5611	-100	
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-5	A
P_D	Total power dissipation	$T_C = 25\square$	25	W
T_j	Junction temperature		150	$\square$
T_{stg}	Storage temperature		-65~150	$\square$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th\ j-c}$	Thermal resistance junction to case	4.37	$\square/W$

Silicon PNP Power Transistors 2N5605 2N5607 2N5609 2N5611

CHARACTERISTICS**T_j=25°C unless otherwise specified**

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	2N5605	$I_C=50mA ; I_B=0$	-60			V
		2N5607/5609		-80			
		2N5611		-100			
V_{CEsat}	Collector-emitter saturation voltage		$I_C=-1A ; I_B=-0.1A$			-0.5	V
V_{BE}	Base-emitter on voltage		$I_C=-2.5A ; V_{CE}=-5V$			-1.5	V
I_{CBO}	Collector cut-off current		$V_{CB}=\text{Rated } V_{CBO} ; I_E=0$			-0.1	mA
I_{CEO}	Collector cut-off current		$V_{CE}=\text{Rated } V_{CEO} ; I_B=0$			-1.0	mA
I_{EBO}	Emitter cut-off current		$V_{EB}=-5V ; I_C=0$			-0.1	mA
h_{FE}	DC current gain	2N5605/5609	$I_C=-2.5A ; V_{CE}=-5V$	70		200	
		2N5607/5611		30		90	
f_T	Transition frequency	2N5605/5609	$I_C=-0.5A ; V_{CE}=-10V$	70			MHz
		2N5607/5611		60			

Silicon PNP Power Transistors 2N5605 2N5607 2N5609 2N5611

PACKAGE OUTLINE

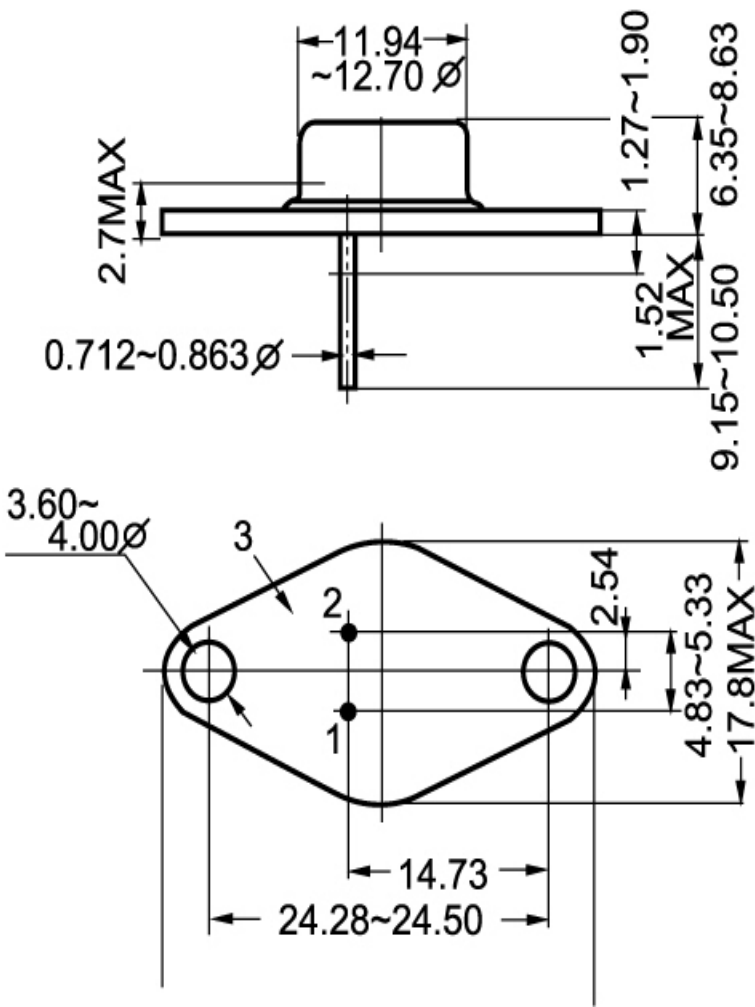


Fig.2 outline dimensions